

METHOD AND APPARATUS FOR CONTROLLING THE CHEMICAL MECHANICAL POLISHING TIME OF
MULTIPLE LAYERS ON A SUBSTRATE

Application No. [NEW] – Attorney Docket No. SEC.1082

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Fig. 1

(PRIOR ART)

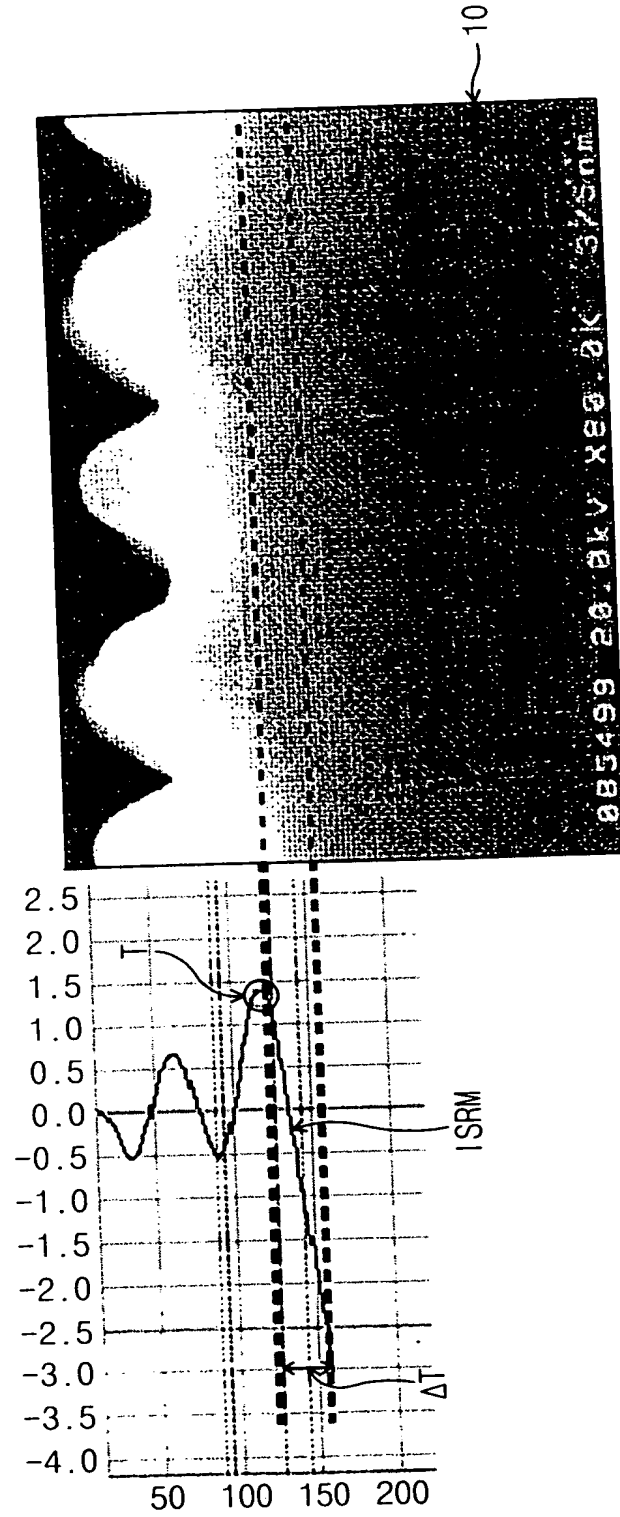


Fig. 2

(PRIOR ART)

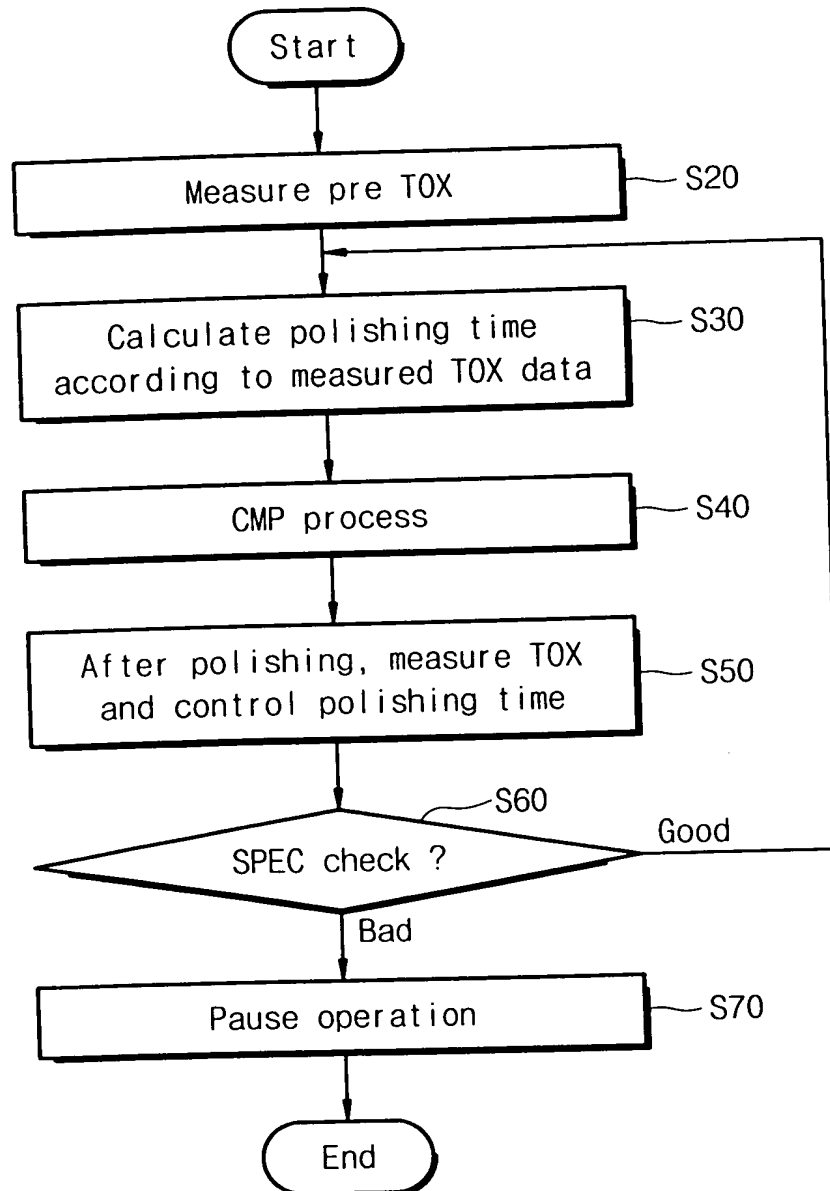


Fig. 3

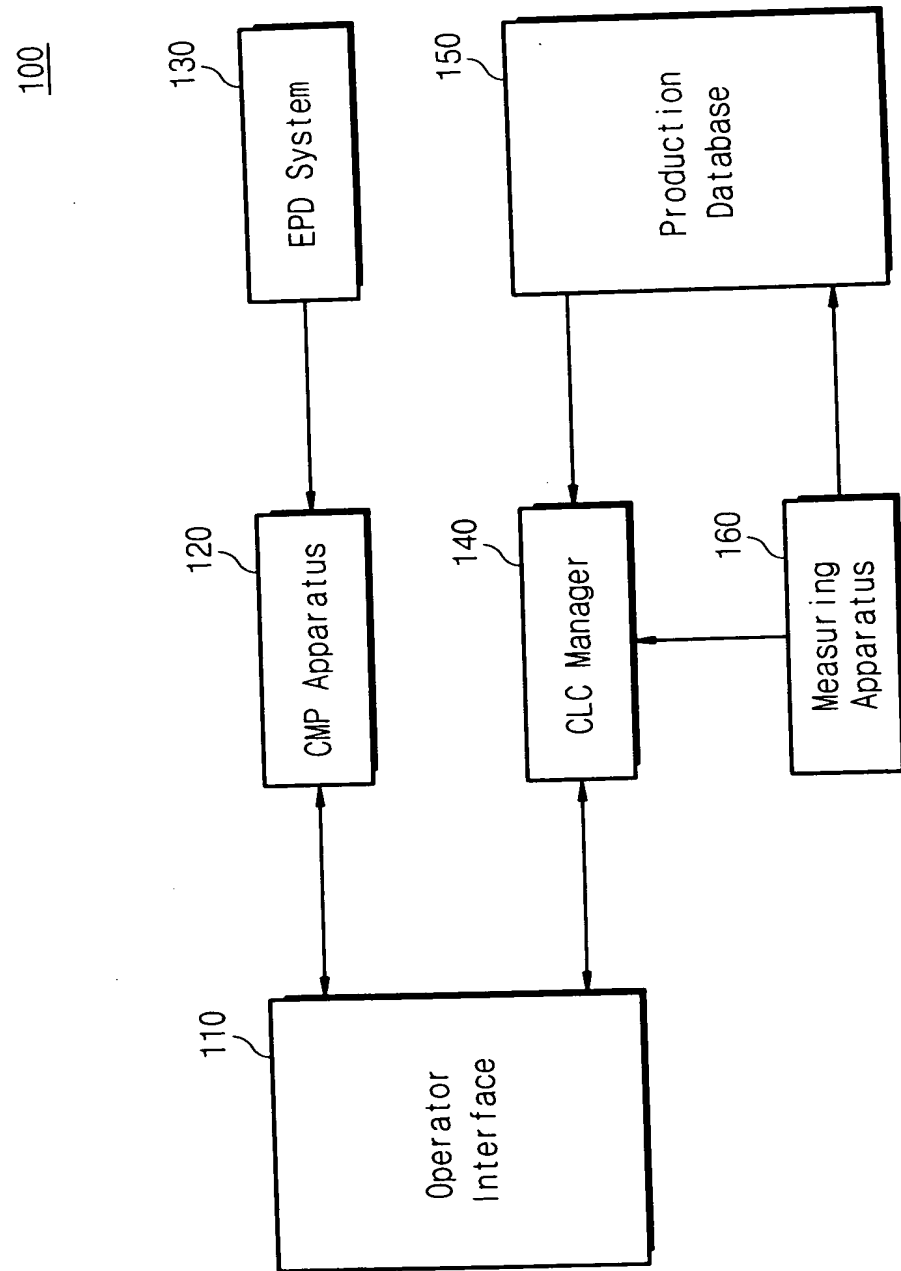


Fig. 4

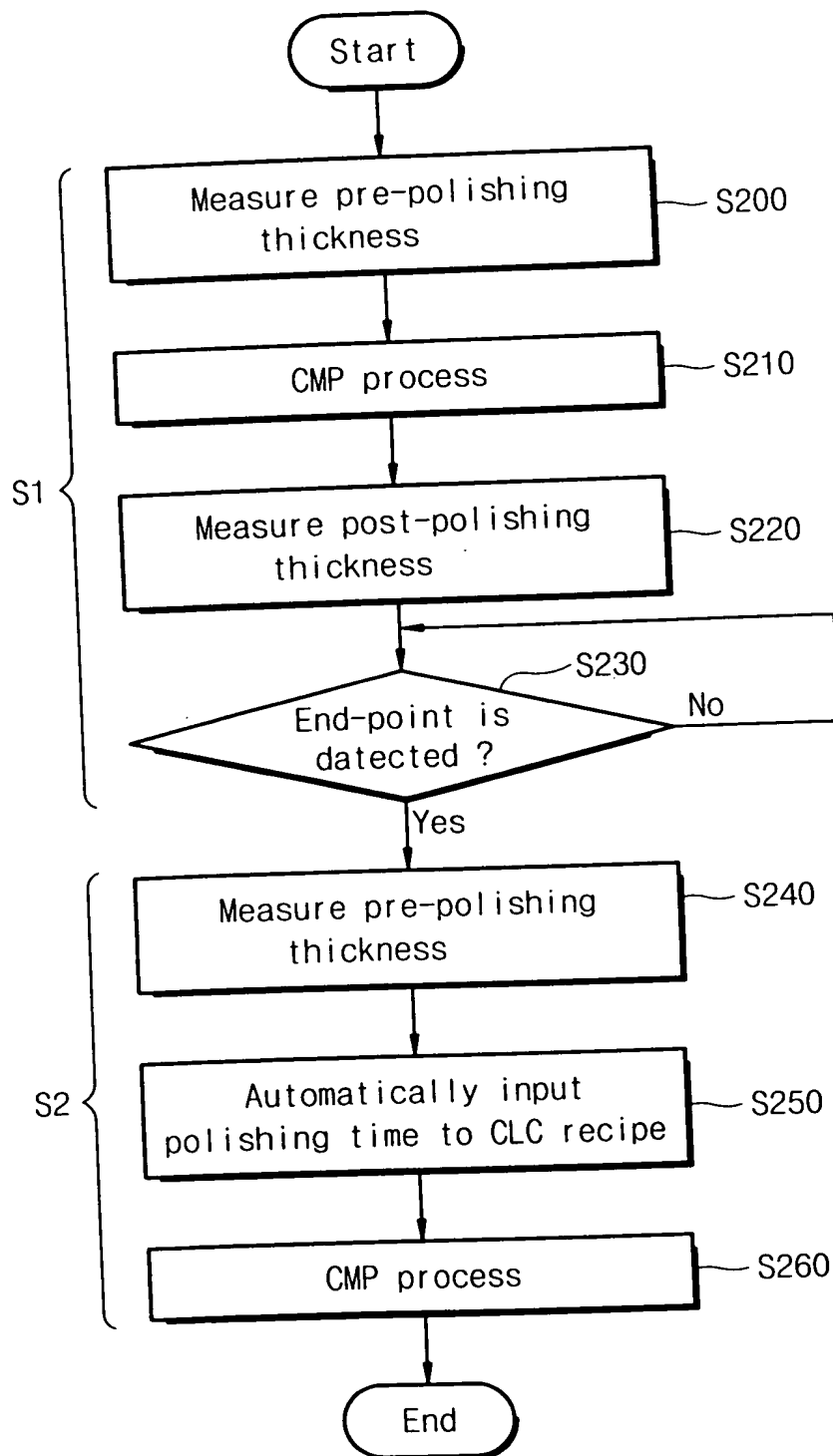


Fig. 5

300

310

320

312

322

Main Polish Step				Main Polish Step			
Step 2: Applying Endpoint				Step 3: CLC Time Control			
Platen:	Angular Velocity	Accel / Decel		Platen:	Angular Velocity	Accel / Decel	
	rpm	rpm/s			rpm	rpm/s	
Head:	Angular Velocity	Accel / Decel		Head:	Angular Velocity	Accel / Decel	
	rpm	rpm/s			rpm	rpm/s	
Sweep: 5.0 sweeps/min From 5.05 in to 5.53 in 5 total zones				Sweep: 5.0 sweeps/min From 5.05 in to 5.53 in 5 total zones			
<input type="checkbox"/> Use Previous Sweep				<input type="checkbox"/> Use Previous Sweep			
Configure Sweep...				Configure Sweep...			
<input type="checkbox"/> Over Ride				<input type="checkbox"/> Over Ride			
Internal Tube	Pressure		psi	Internal Tube	Pressure		psi
Ret Ring	Pressure		psi	Ret Ring	Pressure		psi
Membrane	Pressure		psi	Membrane	Pressure		psi
<input type="checkbox"/> High Pressure Rinse				<input type="checkbox"/> High Pressure Rinse			
Deliv 1:	Slurry		ml/min	Deliv 1:	Slurry		ml/min
Deliv 2:	No Slurry			Deliv 2:	No Slurry		
<input type="checkbox"/> By Endpoint		Max Time: 60.0 s		<input type="checkbox"/> By Time/EP		Max Time: 20.0 s	